

Si Photo-diode Chip—TK0N64PDN

1. Scope

- The specification applies to NIP silicon photo-diode chips.
- Type : TK0N64PDN

2. Structure

- NIP planar type.
- Electrode topside (cathode) : Aluminum.
backside (anode) : Gold.

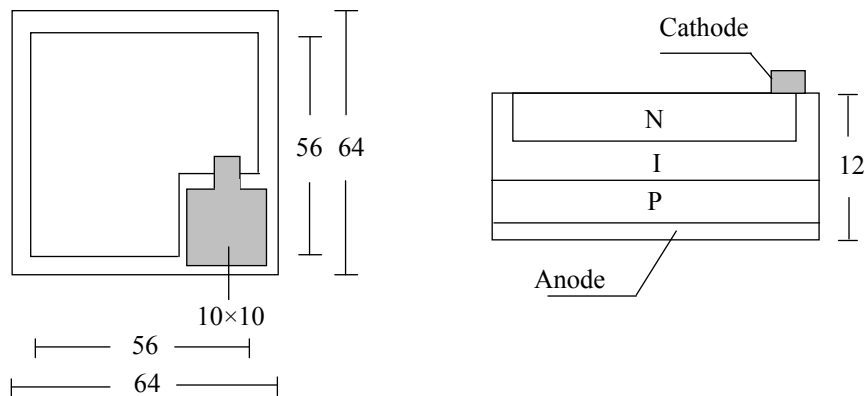
3. Size

- Chip size : $64\text{mil} \times 64\text{mil} \pm 1.5\text{mil}$ ($1.630\text{mm} \times 1.630\text{mm} \pm 0.038\text{mm}$)
- Thickness : $12\text{mil} \pm 1\text{mil}$ ($0.300\text{mm} \pm 0.025\text{mm}$)
- Active area : $56\text{mil} \times 56\text{mil} \pm 0.5\text{mil}$ ($1.420\text{mm} \times 1.420\text{mm} \pm 0.013\text{mm}$)
- Pad size : $10\text{mil} \times 10\text{mil} \pm 0.4\text{mil}$ ($0.250\text{mm} \times 0.250\text{mm} \pm 0.01\text{mm}$)
- Pattern drawing : per fig. 1

4. Electro-Optical Characteristics

($T_a = +25^\circ\text{C}$)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit.
Forward Voltage	V_F	$I_F=10\text{mA}$, $H=0$	0.5		1.3	V
Reverse Breakdown Voltage	V_{BR}	$I_R=100\mu\text{A}$, $H=0$	35			V
Reverse Dark Current	I_D	$V_R=10\text{V}$, $H=0$			10	nA
Light Current	I_L	$V_R=5\text{V}$, Has $1\text{mw}/\text{cm}^2@940\text{nm}$	60			μA
Peak Sensing Wavelength	λ_p			940		nm
Junction Capacitance	C_J	$V_R=3\text{V}$, $F=1\text{MHz}$		14		pF



Unit : mil

fig. 1

2016.Mar



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